IN THE SPECIFICATION:

Please insert the following new paragraph after the Title and before the "TECHNICAL FIELD":

-- RELATED APPLICATIONS

This application is the U.S. National Phase under 35 U.S.C. § 371 of International Application No. PCT/JP2005/005003, filed on March 18, 2005, which in turn claims the benefit of Japanese Application No. 2004-079873, filed on March 19, 2004, the disclosures of which Applications are incorporated by reference herein.–

Please amend the paragraph beginning on page 9 at line 26 and bridging page 10 as follows:

[0031] FIGS. **2(a)** and **2(b)** show an exemplary structure of the substrate **10** made of GaN. FIG. **2(a)** shows the plan structure thereof, and FIG. **2(b)** shows a cross-sectional structure thereof taken along the line ~~VIIIa - VIIIa~~ IIb - IIb in FIG. **2(a)**. As shown in FIG. **2**, the top surface of the substrate **10**, which is an element formation surface, is inclined relative to the (0001) plane **10a** of the plane direction of the GaN crystal, and the angle of inclination (off-angle) is about one degree at a maximum. The direction of inclination is the <11-20> direction, the <10-10> direction, or a direction between the <11-20> direction and the <10-10> direction of the crystal. Note that the (0001) plane of the plane direction means the c-plane in the hexagonal system.

Please amend the paragraph beginning on page 14 at line 2 as follows:

[0044] For the n-type cladding layer **13**, use can be made of a compound whose general formula is represented by $Al_gGa_{1-g}N$ ($0 \leq g < 1$). By employing the n-type cladding layer **13** made of group III-V nitride semiconductor with a wider band gap than the In-containing n-type semiconductor layer **12**, hole overflow from the light-emitting layer **14** can be effectively prevented. Although the n-type cladding layer **13** is preferably doped with an n-type impurity, it may be doped with no n-type impurity. If it is doped with an n-type impurity, it is recommended that the carrier concentration of the cladding layer **13** is lower than those of the n-type contact layer **11** and the In-containing n-type semiconductor layer **12**. By employing such a structure, the n-type

cladding layer **13** has a higher resistance than the n-type contact layer **11**, so that the n-type cladding layer **13** blocks electron flow from the n-type contact layer **11** through the n-type cladding layer **13** toward the light-emitting layer **14**. Thus, electrons spread uniformly at the interface between the In-containing n-type semiconductor layer 12 and ~~within~~ the n-type cladding layer **13**. Therefore, uniform electron injection into the light-emitting layer **14** can be realized to uniformize spatial distribution of light emission from the light-emitting layer **14**. As a result of this, a uniform plane emission of light can be provided from the back surface of the substrate **10** serving as the main light-emitting plane.

Please amend the paragraph beginning on page 18 at line 19 as follows:

[0058] As shown in FIG. **3**, for the conventional stacked film of group III-V nitride semiconductor not provided with the In-containing n-type semiconductor layer **12**, the standard deviation of photoluminescence intensity was 32.9%, which indicates very wide variations. On the other hand, for the stacked film of the present invention made of group III-V nitride semiconductor and provided with the In-containing n-type semiconductor layer **12**, the standard deviation was 4.1%, from which it is obvious that the light-emitting layer **14** is formed uniformly on the substrate.

Please amend the paragraph beginning on page 31 at line 7 as follows:

[0113] Further, a translucent electrode **18** is provided on the top surface of the p-type semiconductor layer **15**, and emitted light is taken from the semiconductor layer formation surface thereof. Provision of the translucent electrode **18** can reduce the area of the p-side electrode **16**, so that light absorption by the p-side electrode **16** can be avoided. Moreover, since the area of the translucent electrode **18** can be increased, a current can be passed uniformly through the light-emitting layer **14**. This enhances the optical power output and reduces the operating voltage. It is sufficient that the translucent electrode **18** is formed of a known indium ~~titanium~~ tin oxide (ITO) film or the like.

Please amend the paragraph beginning on page 33 at line 24 and bridging page 34 as follows:

[0124] An illuminating device according to a fourth embodiment of the present invention will be described below with reference to the accompanying drawings. FIG. **13** shows a cross-sectional structure of a light-emitting unit **60** used for the illuminating device according to the fourth embodiment. Referring to FIG. **13**, the submount **51** with the light-emitting device adhering thereto is allowed to adhere to the inside of a cup of a lead frame **62** in electrically connected relation with Ag paste or the like. The n-side substrate electrode of the submount [[**50**]] **51** is electrically connected to a lead frame **64** with a wire **63** interposed therebetween. The cup of the lead frame **62** is molded with resin **65**.